

C1
forming a gate insulating film in contact with the semiconductor film from the surface of which the contaminating impurity has been removed.

C2
15. (Amended) A method of manufacturing a semiconductor device, comprising steps of:
forming at least one semiconductor island over a substrate;
spinning the substrate;
contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface;
and then

forming a gate insulating film over said semiconductor island.

C3
19. (Amended) A method of manufacturing a semiconductor device, comprising steps of:
forming a semiconductor film over a substrate;
crystallizing said semiconductor film;
forming at least one semiconductor island over said substrate by patterning the crystallized semiconductor film ;
spinning the substrate;
contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface;
and then

forming a gate insulating film over said semiconductor island; and
forming a gate electrode over said gate insulating film.

23. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming gate wirings over a substrate;

spinning the substrate;

contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then

forming a gate insulating film and a semiconductor film over said gate wirings.

27. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming gate wirings over a substrate;

spinning the substrate;

contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then

forming a gate insulating film and a semiconductor film over said gate wirings, continuously.
